

SUBSTITUTE ABSTRACT

A method of manufacturing a semiconductor device uses a slurry for chemical mechanical polishing during the manufacturing process, the slurry containing polishing particles comprising colloidal particles whose primary particles have a diameter ranging from 5 to 30 nm, wherein the degree of association of the primary particles is 5 or less. This slurry for chemical mechanical polishing makes it possible to minimize erosion and scratching whenever a conductive material film is subjected to a CMP treatment.

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